Advanced PECVD-Nitride2(HF n=2.00, 9.3nm/min)			
SiN depostion~3000A, 300C			
Step1:	**NITRIDE2 coat**		
	Name	**Value**	**Changeable**
	Process pressure	800 mtorr	N
	RF setpoint	30 W	N
	stabilization time	15 seconds	N
	step time(m)	**10**	**Y**
	step time(s)	**0**	**Y**
	2%SiH_4 %He	1040	N
	N_2	980	N
	NH_3	17	N
Step2:	**NITRIDE2 deposition**		
	Name	**Value**	**Changeable**
	Process pressure	800 mtorr	N
	RF setpoint	30 W	N
	stabilization time	15 seconds	N
	step time(m)	**30**	**Y**
	step time(s)	**0**	**Y**
	2%SiH_4 %He	1040	N
	N_2	980	N
	NH_3	17	N
Step3: STANDARD PLASMA CLEAN			
	1. pump down		
	Name	**Value**	**Changeable**
	stabilization time	15 seconds	N
	step time(m)	0	N
	step time(s)	30	N
	2. Pre-purge		
	Name	**Value**	**Changeable**
	purge	**1 (Yes/No)**	N
	stabilization time	15 seconds	N
	step time(m)	**1**	**N**
	step time(sec)	0	N
	3.1 High Pressure		
	Name	**Value**	**Changeable**
	Cload position	**50%**	**N**
	Ctune position	**50%**	**N**
	DriveMatch	**1 (Yes/No)**	**N**
	Process pressure	600 mtorr	N
	RF setpoint=300	300 W	N
	Stabilization time	35 seconds	N
	step time(m)	**ENTER TIME**	Y
	step time(s)	0	Y
	CF_4/O_2(5)	500 sccm	N

Advanced PECVD SiN 3000A Typical Film Properties
Deposition rate=9.05nm/min
Refractive index@632.8nm=1.952
Stress=-480.68MPa
HF etch rate=48.32nm/min

For 7min(coat+deposition) run 1min CLEAN